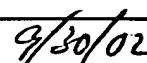


Form PTO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 0819-374		Serial No. Not Yet Assigned	
<b>INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)		Applicant: Takeshi TAKAGI et al.				Filing Date: September 2000 Group: Not Yet Assigned	
		Filing Date: September 2000 Group: Not Yet Assigned					
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)	
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	Document Number	Date	Country	Class	Subclass	Translation Yes No	
WS	6-66519	8/24/94	Japan			Abstract	
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Examiner				Date Considered		9/30/02	
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office		Atty Docket 0819-0374		Serial No. 09/659,484	
INFORMATION DISCLOSURE STATEMENT		Applicants: Takeshi TAKAGI et al.					
		Filing Date: September 11, 2000			Group Art Unit: 2814		
<b>FOREIGN PATENT DOCUMENTS</b>							
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
WSL	01-231371	09/14/1989	JP			Part. Eng. & Abst.	
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Examiner Initial							
WSL	Notice of Reasons of Rejection, Patent Application No. 10-154689 Mailing Date: October 2, 2001, Mailing No. 2033500001, with English Translation						
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Form PTO-1449  
(Rev. 8-83)U.S. Department of Commerce  
Patent and Trademark Office

Atty Docket 0819-0374

Serial No. 09/659,484

## INFORMATION DISCLOSURE STATEMENT

Applicants: Takeshi TAKAGI et al.

Filing Date: September 11, 2000

Group Art Unit: 2814

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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
WSV	803-198344	08/29/1991	JP			Part Eng

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Examiner Initial	Document Description
WSV	Notice of Reasons of Rejection, Patent Application No. 10-154689 Mailing Date: June 4, 2002, Docket No. 2033500001, with Mailing No. 172502

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\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.